EB SERIES TRANSISTORS EB202

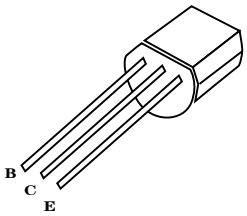
● **FEATURES**：■HIGH VOLTAGE CAPABILITY ■HIGH SPEED SWITCHING ■WIDE SOA

● **APPLICATION:** ■FLUORESCENT LAMP ■ELECTRONIC BALLAST

● Absolute Maximum Ratings（Tc=25°C）

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	600	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter- Base Voltage	V_{EBO}	9	V
Collector Current	I_C	1.0	A
Total Power Dissipation	P_C	12	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65-150	°C

TO-92



● Electronic Characteristics（Tc=25°C）

CHARACTERISTICS	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector-Base Cutoff Current	I_{CBO}	V_{CB}=600V		100	μA
Collector-Emitter Cutoff Current	I_{CEO}	V_{CE}=400V,I_B=0		250	μA
Collector-Emitter Voltage	V_{CEO}	I_C=10mA,I_B=0	400		V
Emitter- Base Voltage	V_{EBO}	I_E=1mA,I_C=0	9		V
Collector-Emitter Saturation Voltage	Vcesat	I_C=0.2A,I_B=0.04A		0.30	V
		I_C=0.75A,I_B=0.25A		0.50	
Base-Emitter Saturation Voltage	Vbesat	I_C=0.2A,I_B=0.04A		1.2	V
DC Current Gain	h_{FE}	V_{CE}=5V,I_C=1mA	7		
		V_{CE}=10V,I_C=0.1A	10	40	
		V_{CE}=5V,I_C=1A	5		
Storage Time	t_S	V_{CC}=5V, I_C=0.1A, (UI9600)	2.0	4.5	μS
Falling Time	tf			1.0	

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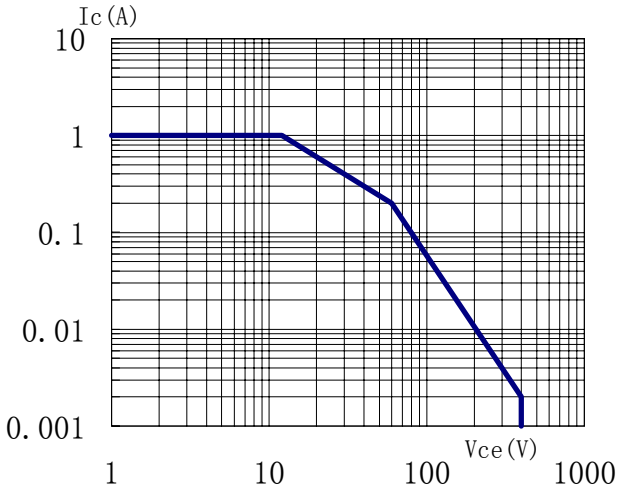
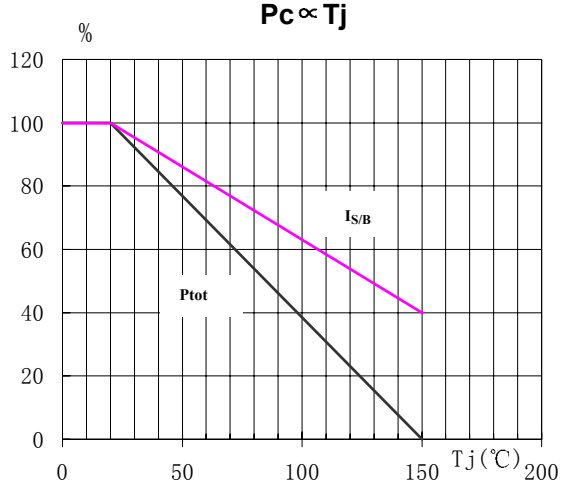
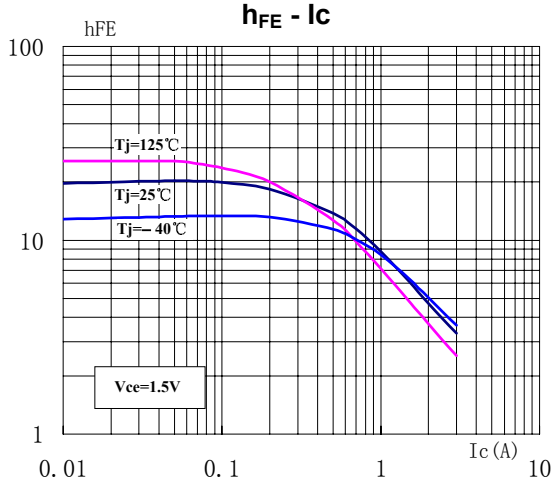
SOA (DC)



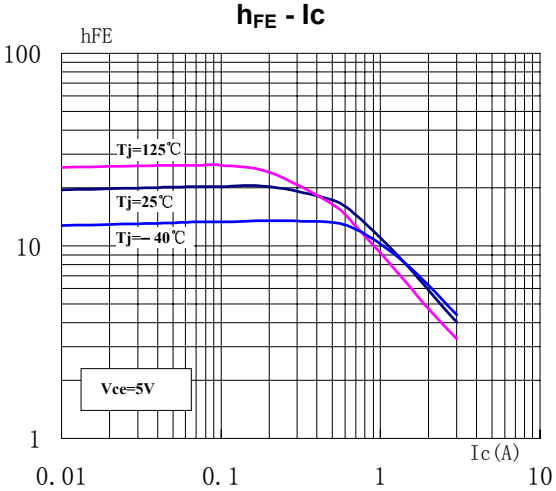
Pc∝Tj



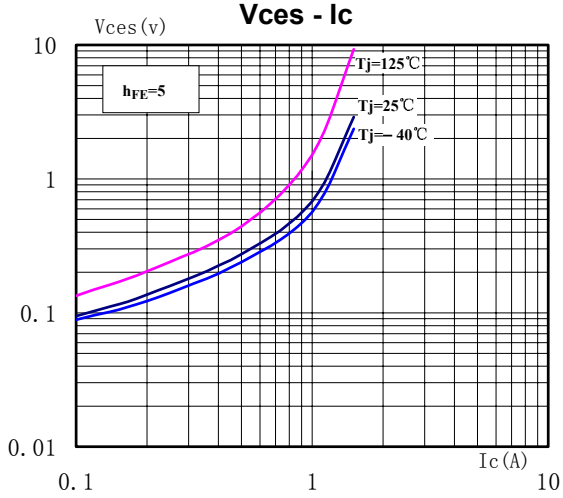
h_{FE} - Ic



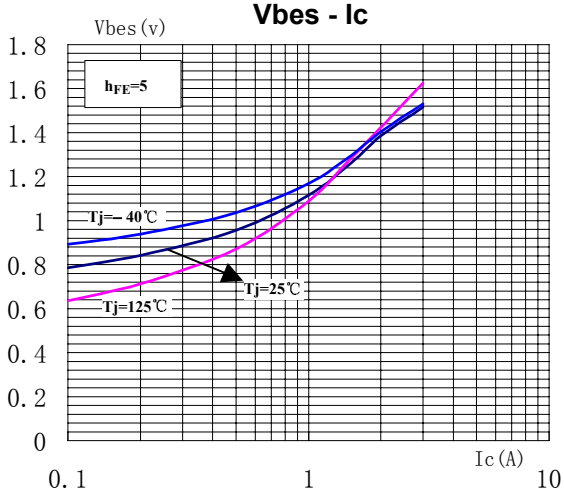
h_{FE} - Ic



Vces - Ic



Vbes - Ic



TO-92 MECHANICAL DATA

UNIT：mm

SYMBOL	min	nom	max
A	4.3		5.3
b	0.3		
c	0.3		
ϕD D	4.3		5.2
d	1.0		1.7
E	3.2		4.2
e		2.54	
e1		1.27	
L	12.7		
L1			2.0